

Title (en)

Method for simultaneously machining both sides of disc-shaped work pieces, especially semiconductor wafers.

Title (de)

Verfahren zum beidseitigen abtragenden Bearbeiten von scheibenförmigen Werkstücken, insbesondere Halbleiterscheiben.

Title (fr)

Procédé pour l'usinage simultané des deux faces de pièces en forme de disque, en particulier de disques semi-conducteurs.

Publication

**EP 0208315 A1 19870114 (DE)**

Application

**EP 86109420 A 19860710**

Priority

DE 3524978 A 19850712

Abstract (en)

[origin: US4739589A] A process is provided for bilateral abrasive machining of wafer-like workpieces, especially semiconductor wafers. The process uses carrier disks in which the outer periphery on which the driving forces mesh, is made of a material having a tensile strength of at least 100 N/mm<sup>2</sup>, while in the area that comes into contact with the workpieces to be machined, there is provided a plastic material having an elasticity modulus of from 1.0 to 8.104 N/mm<sup>2</sup>.

Abstract (de)

Es wird ein Verfahren zum beidseitigen abtragenden Bearbeiten von scheibenförmigen Werkstücken, insbesondere Halbleiterscheiben angegeben. Erfindungsgemäß werden dabei Trägerscheiben eingesetzt, bei denen der Außenumfang, an welchem die Antriebskräfte angreifen, aus einem Werkstoff mit einer Zugfestigkeit von mindestens 100 N/mm<sup>2</sup> gefertigt ist, während im mit den zu bearbeitenden Werkstücken in Kontakt kommenden Bereich ein Kunststoff mit Elastizitätsmodul von 1,0 bis 8·10<sup>4</sup> N/mm<sup>2</sup> vorgesehen ist.

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IPC 8 full level

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CPC (source: EP US)

**B24B 37/08** (2013.01 - EP US)

Citation (search report)

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DOCDB simple family (application)

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